

GDBAT54

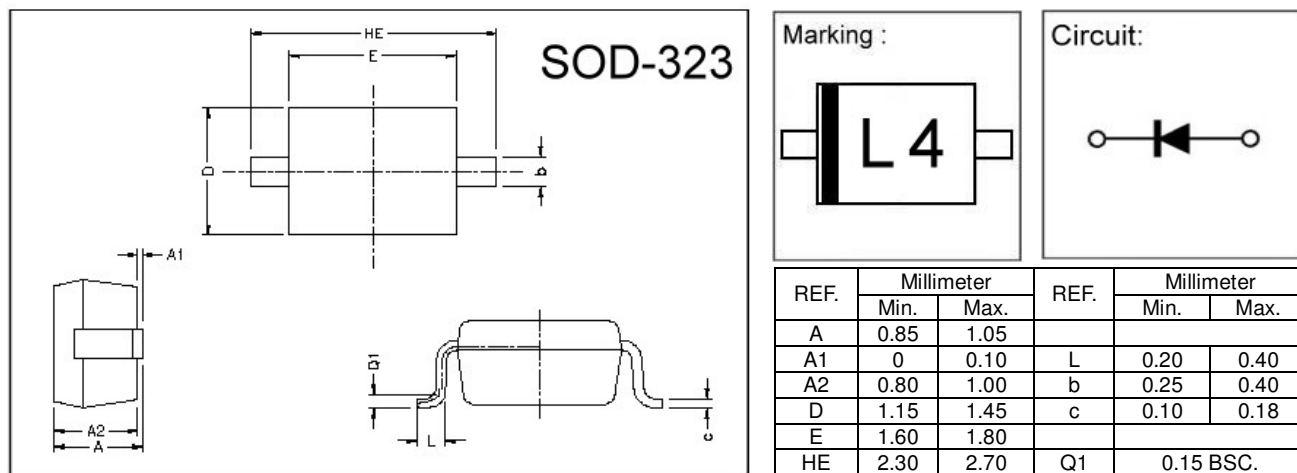
SURFACE MOUNT, SCHOTTKY BARRIER DIODE

VOLTAGE 30V, CURRENT 200mA

Description

The GDBAT54 is designed for high speed switching applications circuit protection, and voltage clamping.

Package Dimensions



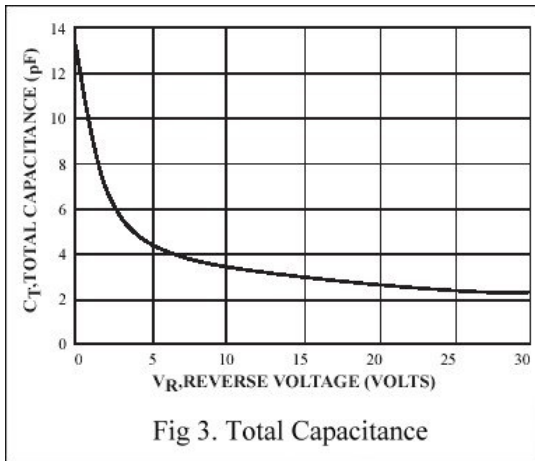
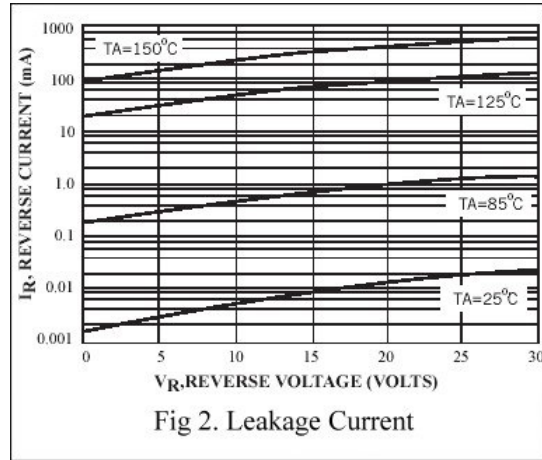
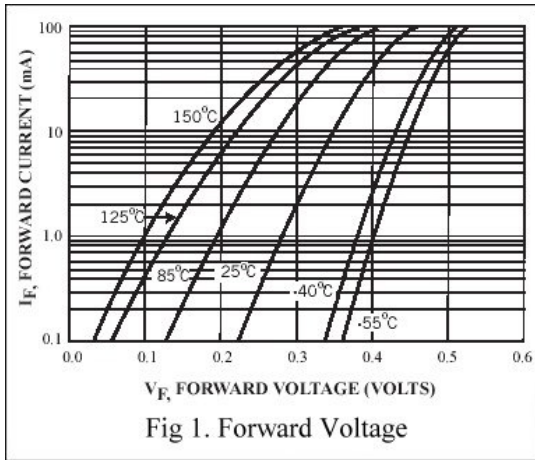
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	-55 ~ +125	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Peak Repetitive Reverse Voltage	V _R	30	V
Forward Continuous Current	I _F	200	mA
Peak Repetitive Forward Current	I _{FRM}	300	mA
Surge Forward Current(t ≤ 1.0s)	I _{FSM}	600	mA
Total Power Dissipation at Ta = 25°C	PD	225	mW

Characteristics at Ta = 25°C

characteristics	Symbol	Min	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V _{(BR)R}	30	-	V	I _R =10μA
Forward Voltage	V _{F(1)}	-	240	mV	I _F =0.1mA
	V _{F(2)}	-	320	mV	I _F =1mA
	V _{F(3)}	-	400	mV	I _F =10mA
	V _{F(4)}	-	500	mV	I _F =30mA
	V _{F(5)}	-	1000	mV	I _F =100mA
Reverse Leakage Current	I _R	-	2.0	μA	V _R =25V
Total Capacitance	C _T	-	10	pF	V _R =1V, f=1MHz
Reverse Recover Time	T _{rr}	-	5	ns	I _F =I _R =10mA, I _{R(Rec)} =1mA

Characteristics Curve



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